

In the Claims

1. - 10. (canceled)

11. (new) A semiconductor device comprising:

first and second adjacent spaced parallel conductive lines, with each conductive line having a width and a length, wherein the length is greater than the width; and

a dielectric layer interposed between, and extending directly over, the first and second parallel spaced conductive lines wherein the dielectric layer comprises an opening therein,

wherein in a cross section taken across and perpendicular with the first and second parallel spaced conductive lines, the cross section comprises:

a cross sectional area of the first conductive line and of the second conductive line, wherein the cross sectional area of the first conductive line is about equal to the cross sectional area of the second conductive line; and

a cross section of the dielectric layer which comprises dielectric material having the opening therein, wherein the opening has a cross sectional area which is about equal to the size and shape of the cross sectional area of each of the first and second conductive lines.

12. (new) The semiconductor device of claim 11 wherein the cross section further comprises the dielectric material overlying both the first and second conductive lines.

13. (new) The semiconductor device of claim 11 wherein the opening in the dielectric layer is a first opening and the cross section further comprises an etched second opening in the dielectric layer which extends through a top surface of the dielectric layer and connects with the first opening in the dielectric layer.

14. (new) The semiconductor device of claim 13 wherein the etched second opening, in a section taken in a plane parallel with an upper surface of the dielectric layer, has a round or oval shape.

15. (new) The semiconductor device of claim 13 wherein the dielectric layer is a first dielectric layer and the semiconductor device further comprises a second dielectric layer which fills the etched second opening and leaves the first opening unfilled.

16. (new) The semiconductor device of claim 11 wherein the opening in the dielectric layer is a first opening and, in the cross section, the dielectric layer further comprises second and third openings therein wherein, in the cross section, the second and third openings each have an area which is smaller than the first opening and wherein the first opening is interposed between the second and third openings.

17. (new) The semiconductor device of claim 16 wherein each of the second and third openings, in the cross section, have an area which is between about 0.25 and about 0.75 times the cross sectional area of the first opening.